

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FUJI:200

Application Number

NEW APPL

Applicant(s)

Takashi KOBAYASHI et al.

Filing Date

October 31, 2001

Group Art Unit

U.S. PTO
10/020573
10/31/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EC	US	4,412,242	10/83	Herman et al.	357	52	
EC	US	4,399,449	8/83	Herman et al.	357	53	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EC		"Optimization and Surface Charge Sensitivity of High-Voltage Blocking Structures with Shallow Junctions"; Hamza Yilmaz; July 1991; IEEE Transactions on Electron Devices, Vol. 38, No. 7; pages 1666-1675.
EC		"A Parametric Study of Power Mosfets"; Chenming Hu; Proceedings of the Conference of Rec. Power Electronics Specialists, 1979 IEEE; pages 385-395.

EXAMINER <i>[Signature]</i>	DATE CONSIDERED 12/13/02
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

